

# AUIRGR4045D

# AUIRGU4045D

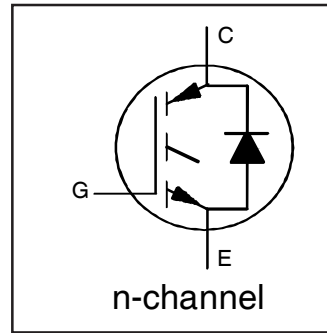
## INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

### Features

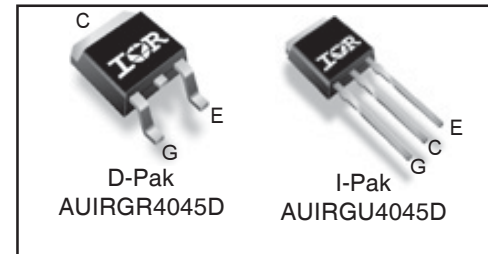
- Low  $V_{CE(on)}$  Trench IGBT Technology
- Low Switching Losses
- Maximum Junction temperature 175 °C
- 5µs SCSOA
- Square RBSOA
- 100% of the parts tested for  $I_{LM}$ ①
- Positive  $V_{CE(on)}$  Temperature Coefficient.
- Ultra Fast Soft Recovery Co-pak Diode
- Tighter Distribution of Parameters
- Lead-Free, RoHS Compliant
- Automotive Qualified\*

### Benefits

- High Efficiency in a Wide Range of Applications
- Suitable for a Wide Range of Switching Frequencies due to Low  $V_{CE(ON)}$  and Low Switching Losses
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation
- Low EMI



|                                 |
|---------------------------------|
| $V_{CES} = 600V$                |
| $I_C = 6.0A, T_C = 100^\circ C$ |
| $V_{CE(on) typ.} = 1.7V$        |



| G    | C         | E       |
|------|-----------|---------|
| Gate | Collector | Emitter |

### Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ( $T_A$ ) is 25°C, unless otherwise specified.

|                                         | Parameter                                               | Max.                              | Units |
|-----------------------------------------|---------------------------------------------------------|-----------------------------------|-------|
| V <sub>CES</sub>                        | Collector-to-Emitter Breakdown Voltage                  | 600                               | V     |
| I <sub>C</sub> @ T <sub>C</sub> = 25°C  | Continuous Collector Current                            | 12                                | A     |
| I <sub>C</sub> @ T <sub>C</sub> = 100°C | Continuous Collector Current                            | 6.0                               |       |
| I <sub>CM</sub>                         | Pulsed Collector Current, V <sub>GE</sub> = 15V         | 18                                |       |
| I <sub>LM</sub>                         | Clamped Inductive Load Current, V <sub>GE</sub> = 20V ① | 24                                |       |
| I <sub>F</sub> @T <sub>C</sub> =25°C    | Diode Continuous Forward Current                        | 8.0                               |       |
| I <sub>F</sub> @T <sub>C</sub> =100°C   | Diode Continuous Forward Current                        | 4.0                               |       |
| I <sub>FM</sub>                         | Diode Maximum Forward Current ②                         | 24                                |       |
| V <sub>GE</sub>                         | Continuous Gate-to-Emitter Voltage                      | ± 20                              | V     |
|                                         | Transient Gate-to-Emitter Voltage                       | ± 30                              |       |
| P <sub>D</sub> @ T <sub>C</sub> =25°    | Maximum Power Dissipation                               | 77                                | W     |
| P <sub>D</sub> @ T <sub>C</sub> =100°   | Maximum Power Dissipation                               | 39                                |       |
| T <sub>J</sub>                          | Operating Junction and                                  | -55 to + 175                      | °C    |
| T <sub>STG</sub>                        | Storage Temperature Range                               |                                   |       |
|                                         | Soldering Temperature, for 10 seconds                   | 300 (0.063 in. (1.6mm) from case) |       |

### Thermal Resistance

|                 | Parameter                         | Min. | Typ. | Max. U | nits |
|-----------------|-----------------------------------|------|------|--------|------|
| $R_{\theta JC}$ | Junction-to-Case - IGBT ③         | —    | —    | 1.9    | °C/W |
| $R_{\theta JC}$ | Junction-to-Case - Diode ③        | —    | —    | 6.8    |      |
| $R_{\theta JA}$ | Junction-to-Ambient (PCB Mount) ⑤ | —    | —    | 50     |      |
| $R_{\theta JA}$ | Junction-to-Ambient               | —    | —    | 110    |      |

\*Qualification standards can be found at <http://www.irf.com/>

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

|                                 | Parameter                               | Min. | Typ. | Max.      | Units   | Conditions                                            | Ref.Fig           |
|---------------------------------|-----------------------------------------|------|------|-----------|---------|-------------------------------------------------------|-------------------|
| $V_{(BR)CES}$                   | Collector-to-Emitter Breakdown Voltage  | 600  | —    | —         | V       | $V_{GE} = 0V, I_C = 100\mu A$ ④                       | CT6               |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temperature Coeff. of Breakdown Voltage | —0   | .36  | —         | V/°C    | $V_{GE} = 0V, I_C = 250\mu A$ ( 25 -175 °C ) ④        |                   |
| $V_{CE(on)}$                    | Collector-to-Emitter Saturation Voltage | —1   | .7   | 2.0       | V       | $I_C = 6.0A, V_{GE} = 15V, T_J = 25^\circ\text{C}$    | 5,6,7,9,<br>10,11 |
|                                 |                                         | —    | 2.07 | —         |         | $I_C = 6.0A, V_{GE} = 15V, T_J = 150^\circ\text{C}$   |                   |
|                                 |                                         | —2   | .14  | —         |         | $I_C = 6.0A, V_{GE} = 15V, T_J = 175^\circ\text{C}$   |                   |
| $V_{GE(th)}$                    | Gate Threshold Voltage                  | 3.5  | —    | 6.5       | V       | $V_{CE} = V_{GE}, I_C = 150\mu A$                     | 9,10,11,12        |
| $\Delta V_{GE(th)}/\Delta T_J$  | Threshold Voltage temp. coefficient     | —    | -13  | —         | mV/°C   | $V_{CE} = V_{GE}, I_C = 250\mu A$ ( 25 -175 °C )      |                   |
| $g_{fe}$                        | Forward Transconductance                | —    | 5.8  | —         | S       | $V_{CE} = 25V, I_C = 6.0A, PW = 80\mu s$              |                   |
| $I_{CES}$                       | Collector-to-Emitter Leakage Current    | —    | —    | 25        | $\mu A$ | $V_{GE} = 0V, V_{CE} = 600V$                          | 8                 |
|                                 |                                         | —    | —    | 250       |         | $V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$ |                   |
| $V_{FM}$                        | Diode Forward Voltage Drop              | —    | 1.60 | 2.30      | V       | $I_F = 6.0A$                                          |                   |
|                                 |                                         | —    | 1.30 | —         |         | $I_F = 6.0A, T_J = 175^\circ\text{C}$                 |                   |
| $I_{GES}$                       | Gate-to-Emitter Leakage Current         | —    | —    | $\pm 100$ | nA      | $V_{GE} = \pm 20V$                                    |                   |

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

|              | Parameter                            | Min.        | Typ. | Max. | Units   | Conditions                                                                                                             | Ref.Fig                  |
|--------------|--------------------------------------|-------------|------|------|---------|------------------------------------------------------------------------------------------------------------------------|--------------------------|
| $Q_g$        | Total Gate Charge (turn-on)          | —           | 13   | 19.5 | nC      | $I_C = 6.0A$                                                                                                           | 24<br>CT1                |
| $Q_{ge}$     | Gate-to-Emitter Charge (turn-on)     | —           | 3.1  | 4.65 |         | $V_{CC} = 400V$                                                                                                        |                          |
| $Q_{gc}$     | Gate-to-Collector Charge (turn-on)   | —           | 6.4  | 9.6  |         | $V_{GE} = 15V$                                                                                                         |                          |
| $E_{on}$     | Turn-On Switching Loss               | —           | 56   | 86   | $\mu J$ | $I_C = 6.0A, V_{CC} = 400V, V_{GE} = 15V$                                                                              | CT4                      |
| $E_{off}$    | Turn-Off Switching Loss              | —           | 122  | 143  |         | $R_G = 47\Omega, L = 1mH, L_S = 150nH, T_J = 25^\circ\text{C}$                                                         |                          |
| $E_{total}$  | Total Switching Loss                 | —           | 178  | 229  |         | Energy losses include tail and diode reverse recovery                                                                  |                          |
| $t_{d(on)}$  | Turn-On delay time                   | —           | 27   | 35   | ns      | $I_C = 6.0A, V_{CC} = 400V$                                                                                            | CT4                      |
| $t_r$        | Rise time                            | —           | 11   | 15   |         | $R_G = 47\Omega, L = 1mH, L_S = 150nH$                                                                                 |                          |
| $t_{d(off)}$ | Turn-Off delay time                  | —           | 75   | 93   |         | $T_J = 25^\circ\text{C}$                                                                                               |                          |
| $t_f$        | Fall time                            | —           | 17   | 22   |         |                                                                                                                        |                          |
| $E_{on}$     | Turn-On Switching Loss               | —           | 140  | —    | $\mu J$ | $I_C = 6.0A, V_{CC} = 400V, V_{GE} = 15V$                                                                              | 13,15<br>CT4<br>WF1,WF2  |
| $E_{off}$    | Turn-Off Switching Loss              | —           | 189  | —    |         | $R_G = 47\Omega, L = 1mH, L_S = 150nH, T_J = 175^\circ\text{C}$                                                        |                          |
| $E_{total}$  | Total Switching Loss                 | —           | 329  | —    |         | Energy losses include tail and diode reverse recovery                                                                  |                          |
| $t_{d(on)}$  | Turn-On delay time                   | —           | 26   | —    | s       | $I_C = 6.0A, V_{CC} = 400V$                                                                                            | 14,16<br>CT4<br>WF1,WF2  |
| $t_r$        | Rise time                            | —           | 12   | —n   |         | $R_G = 47\Omega, L = 1mH, L_S = 150nH$                                                                                 |                          |
| $t_{d(off)}$ | Turn-Off delay time                  | —           | 95   | —    |         | $T_J = 175^\circ\text{C}$                                                                                              |                          |
| $t_f$        | Fall time                            | —           | 32   | —    |         |                                                                                                                        |                          |
| $C_{ies}$    | Input Capacitance                    | —           | 350  | —    | pF      | $V_{GE} = 0V$                                                                                                          | 23                       |
| $C_{oes}$    | Output Capacitance                   | —           | 29   | —    |         | $V_{CC} = 30V$                                                                                                         |                          |
| $C_{res}$    | Reverse Transfer Capacitance         | —           | 10   | —    |         | $f = 1Mhz$                                                                                                             |                          |
| RBSOA        | Reverse Bias Safe Operating Area     | FULL SQUARE |      |      |         | $T_J = 175^\circ\text{C}, I_C = 24A$<br>$V_{CC} = 500V, V_p = 600V$<br>$R_G = 100\Omega, V_{GE} = +20V \text{ to } 0V$ | 4<br>CT2                 |
| SCSOA        | Short Circuit Safe Operating Area    | —           | 5    | —    | $\mu s$ | $V_{CC} = 400V, V_p = 600V$<br>$R_G = 100\Omega, V_{GE} = +15V \text{ to } 0V$                                         | 22<br>CT3, WF4           |
| $E_{rec}$    | Reverse recovery energy of the diode | —           | 178  | —    | $\mu J$ | $T_J = 175^\circ\text{C}$                                                                                              | 17,18,19<br>20,21<br>WF3 |
| $t_{rr}$     | Diode Reverse recovery time          | —           | 74   | —    | ns      | $V_{CC} = 400V, I_F = 6.0A$                                                                                            |                          |
| $I_{rr}$     | Peak Reverse Recovery Current        | —           | 12   | —    | A       | $V_{GE} = 15V, R_G = 47\Omega, L = 1mH, L_S = 150nH$                                                                   |                          |

### Notes:

- ①  $V_{CC} = 80\% (V_{CES}), V_{GE} = 15V, L = 1.0mH, R_G = 47\Omega$ .
- ② Pulse width limited by max. junction temperature.
- ③  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .
- ④ Refer to AN-1086 for guidelines for measuring  $V_{(BR)CES}$  safely.
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

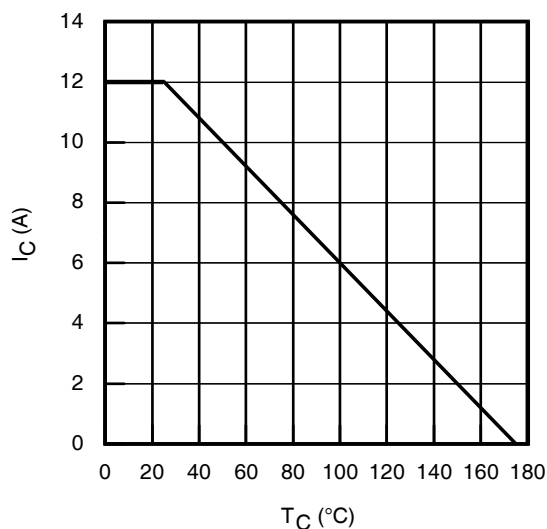
## Qualification Information<sup>†</sup>

|                            |                      |                                                                                                                                                                         |      |
|----------------------------|----------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|
| Qualification Level        |                      | Automotive<br>(per AEC-Q101) <sup>††</sup>                                                                                                                              |      |
|                            |                      | Comments: This part number(s) passed Automotive qualification. IR’s Industrial and Consumer qualification level is granted by extension of the higher Automotive level. |      |
| Moisture Sensitivity Level |                      | D-Pak                                                                                                                                                                   | MSL1 |
|                            |                      | I-PAK                                                                                                                                                                   |      |
| ESD                        | Machine Model        | Class M2 (+/- 200V) <sup>†††</sup><br>AEC-Q101-002                                                                                                                      |      |
|                            | Human Body Model     | Class H1A (+/- 500V) <sup>†††</sup><br>AEC-Q101-001                                                                                                                     |      |
|                            | Charged Device Model | Class C5 (+/- 1000V) <sup>†††</sup><br>AEC-Q101-005                                                                                                                     |      |
| RoHS Compliant             |                      | Yes                                                                                                                                                                     |      |

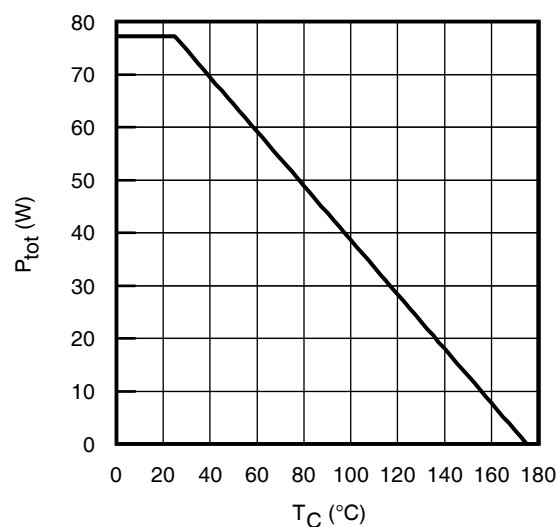
<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com>

<sup>††</sup> Exceptions to AEC-Q101 requirements are noted in the qualification report.

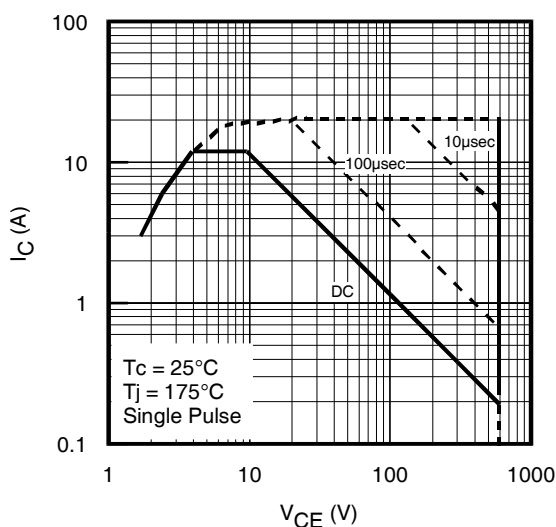
<sup>†††</sup> Highest passing voltage.



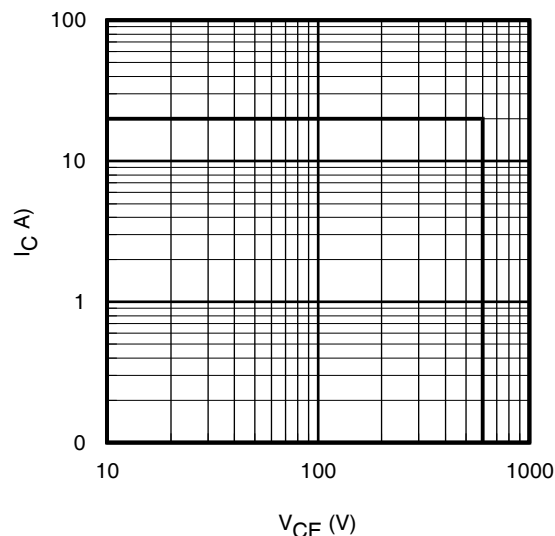
**Fig. 1** - Maximum DC Collector Current vs. Case Temperature



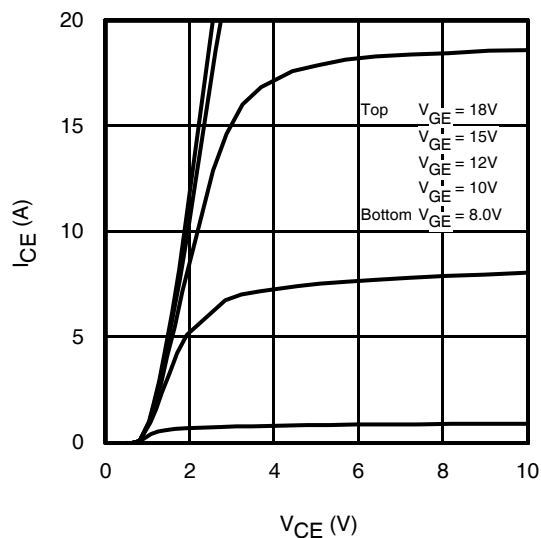
**Fig. 2** - Power Dissipation vs. Case Temperature



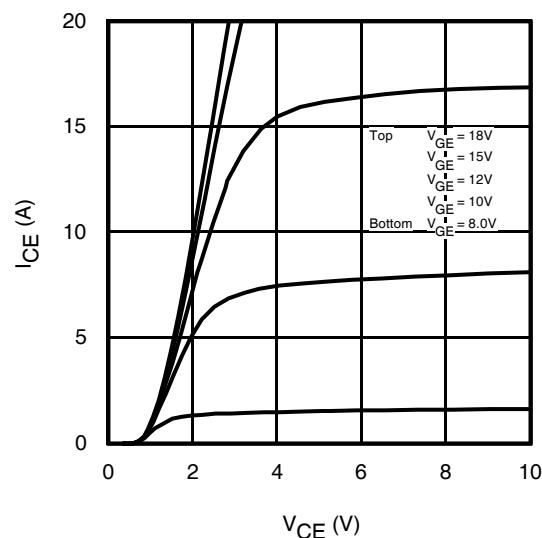
**Fig. 3** - Forward SOA,  
 $T_C = 25^\circ\text{C}$ ,  $T_J \leq 175^\circ\text{C}$ ,  $V_{GE} = 15\text{V}$



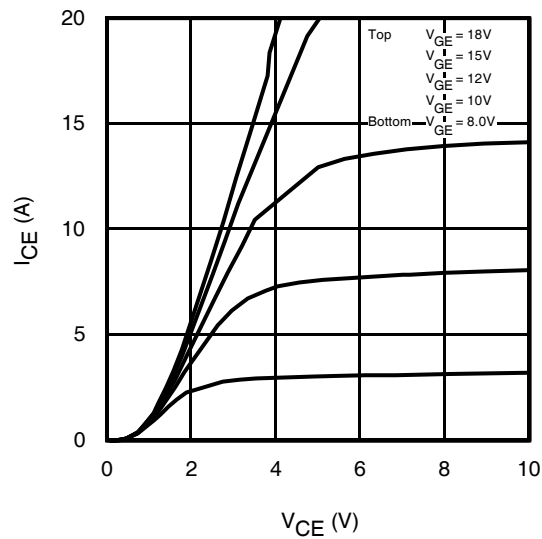
**Fig. 4** - Reverse Bias SOA  
 $T_J = 175^\circ\text{C}$ ,  $V_{GE} = 20\text{V}$



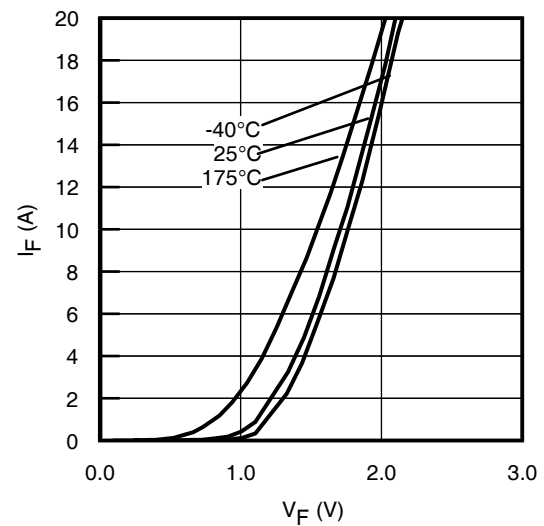
**Fig. 5** - Typ. IGBT Output Characteristics  
 $T_J = -40^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



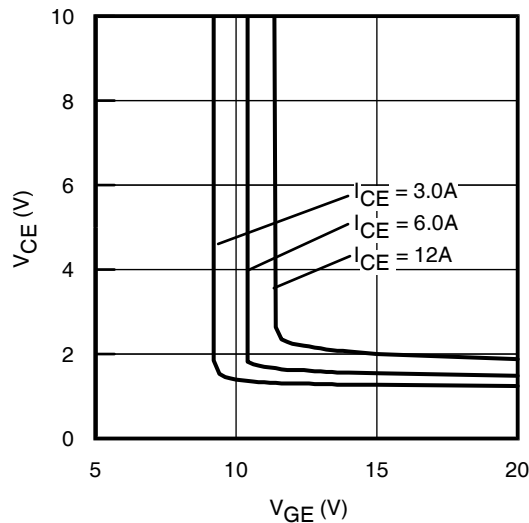
**Fig. 6** - Typ. IGBT Output Characteristics  
 $T_J = 25^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



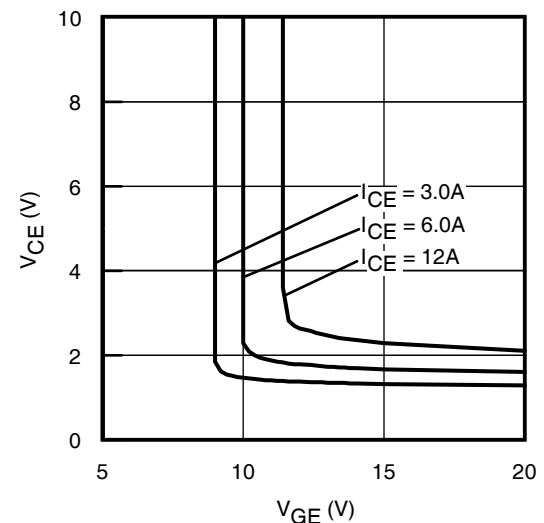
**Fig. 7** - Typ. IGBT Output Characteristics  
 $T_J = 175^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



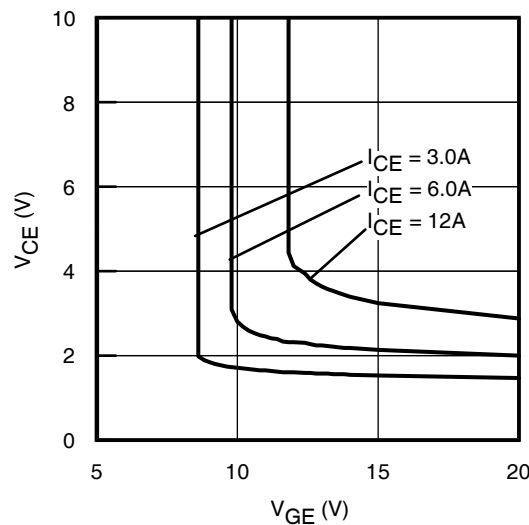
**Fig. 8** - Typ. Diode Forward Characteristics  
 $t_p = 80\mu\text{s}$



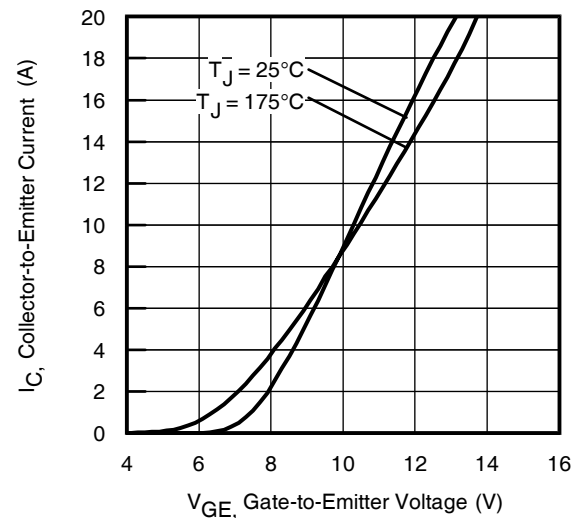
**Fig. 9** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = -40^\circ\text{C}$



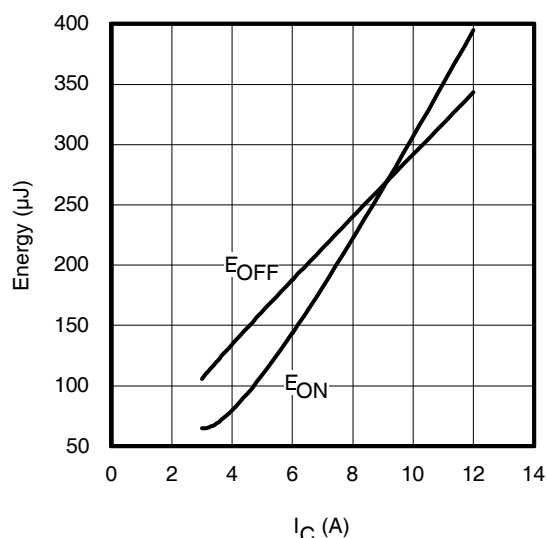
**Fig. 10** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 25^\circ\text{C}$



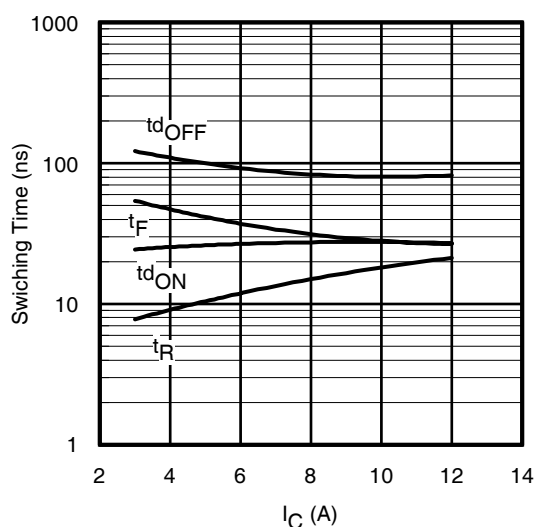
**Fig. 11** - Typical  $V_{CE}$  vs.  $V_{GE}$   
 $T_J = 175^\circ\text{C}$



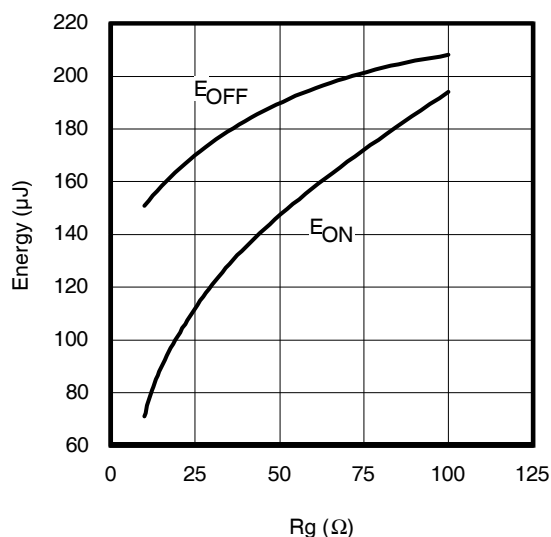
**Fig. 12** - Typ. Transfer Characteristics  
 $V_{CE} = 50\text{V}$ ;  $t_p = 10\mu\text{s}$



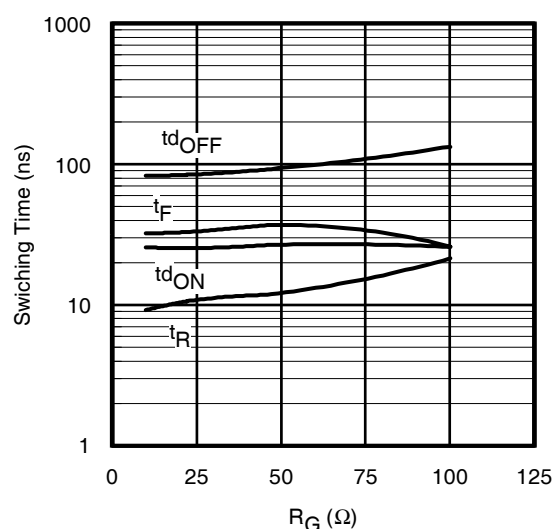
**Fig. 13** - Typ. Energy Loss vs.  $I_C$   
 $T_J = 175^\circ\text{C}$ ;  $L = 1\text{mH}$ ;  $V_{CE} = 400\text{V}$ ;  $R_G = 47\Omega$ ;  $V_{GE} = 15\text{V}$ .



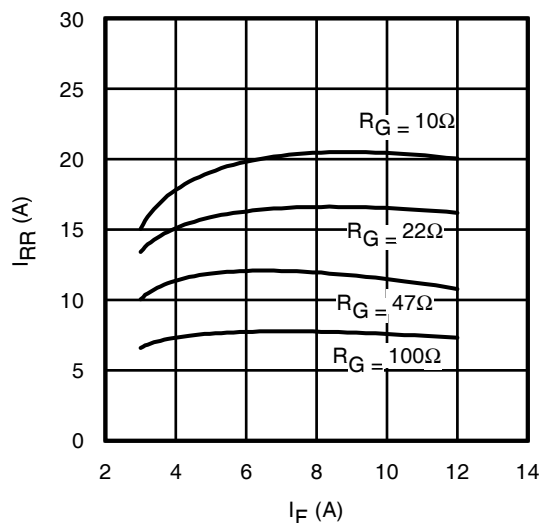
**Fig. 14** - Typ. Switching Time vs.  $I_C$   
 $T_J = 175^\circ\text{C}$ ;  $L = 1\text{mH}$ ;  $V_{CE} = 400\text{V}$   
 $R_G = 47\Omega$ ;  $V_{GE} = 15\text{V}$



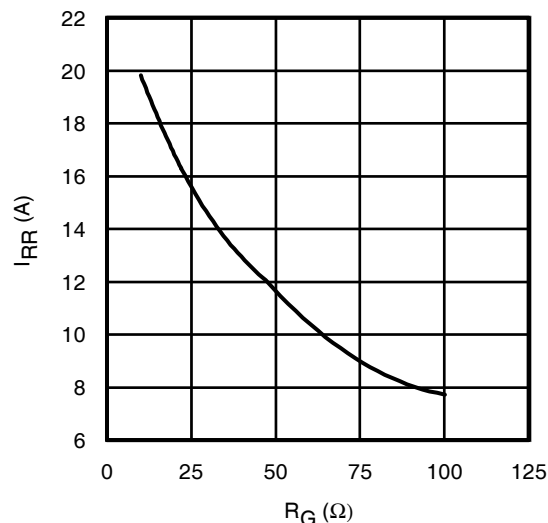
**Fig. 15** - Typ. Energy Loss vs.  $R_G$   
 $T_J = 175^\circ\text{C}$ ;  $L = 1\text{mH}$ ;  $V_{CE} = 400\text{V}$ ;  $I_{CE} = 6.0\text{A}$ ;  $V_{GE} = 15\text{V}$



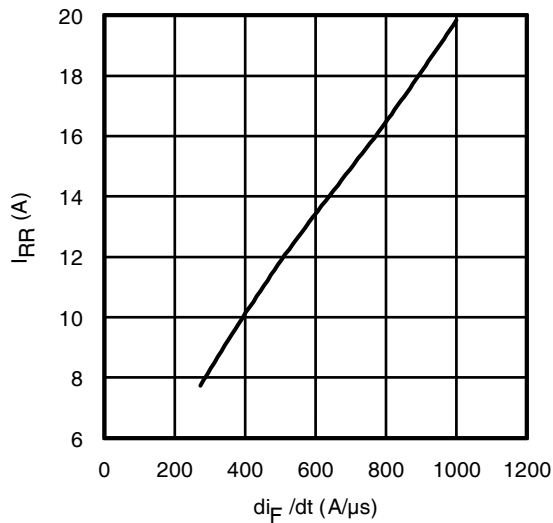
**Fig. 16** - Typ. Switching Time vs.  $R_G$   
 $T_J = 175^\circ\text{C}$ ;  $L = 1\text{mH}$ ;  $V_{CE} = 400\text{V}$   
 $I_{CE} = 6.0\text{A}$ ;  $V_{GE} = 15\text{V}$



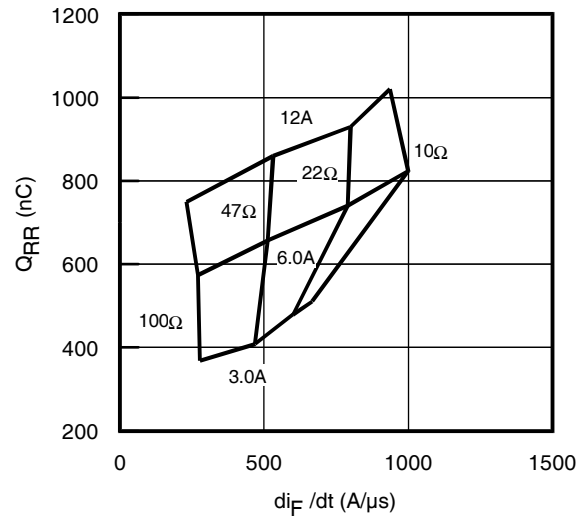
**Fig. 17** - Typical Diode  $I_{RR}$  vs.  $I_F$   
 $T_J = 175^\circ\text{C}$



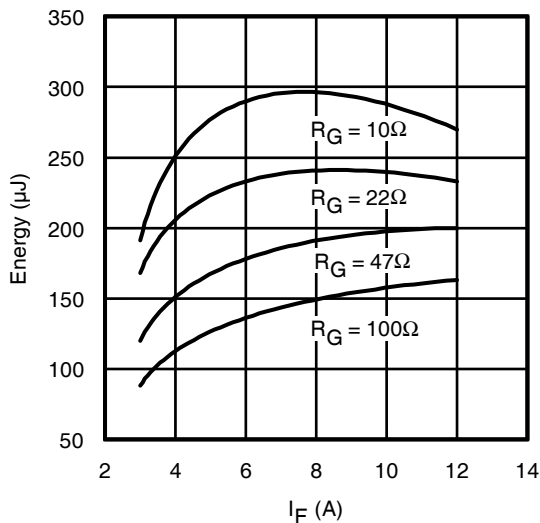
**Fig. 18** - Typical Diode  $I_{RR}$  vs.  $R_G$   
 $T_J = 175^\circ\text{C}$ ;  $I_F = 6.0\text{A}$



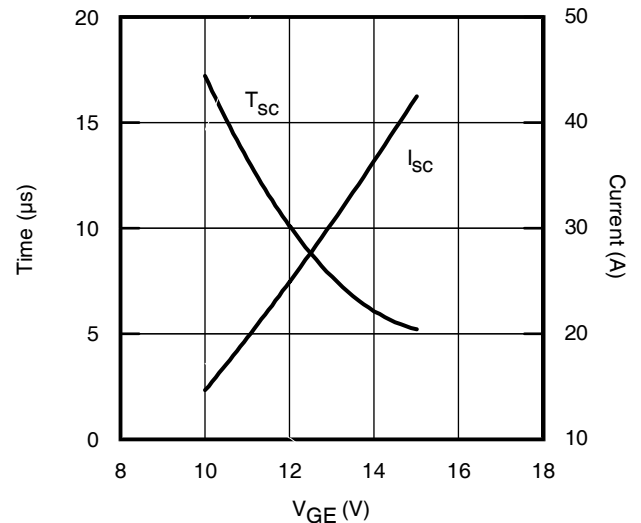
**Fig. 19** - Typical Diode  $I_{RR}$  vs.  $di_F/dt$   
 $V_{CC} = 400V$ ;  $V_{GE} = 15V$ ;  
 $I_{CE} = 6.0A$ ;  $T_J = 175^\circ C$



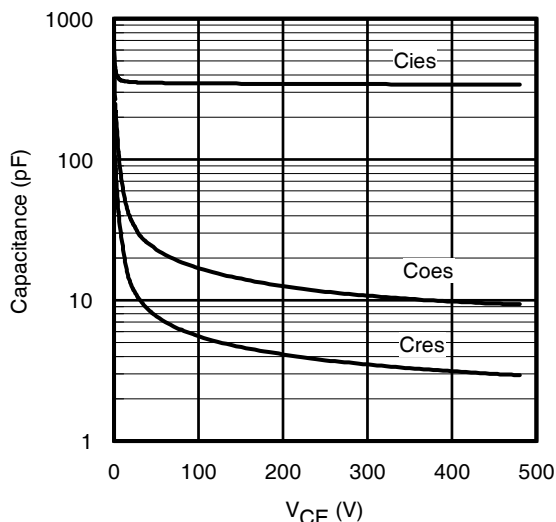
**Fig. 20** - Typical Diode  $Q_{RR}$   
 $V_{CC} = 400V$ ;  $V_{GE} = 15V$ ;  $T_J = 175^\circ C$



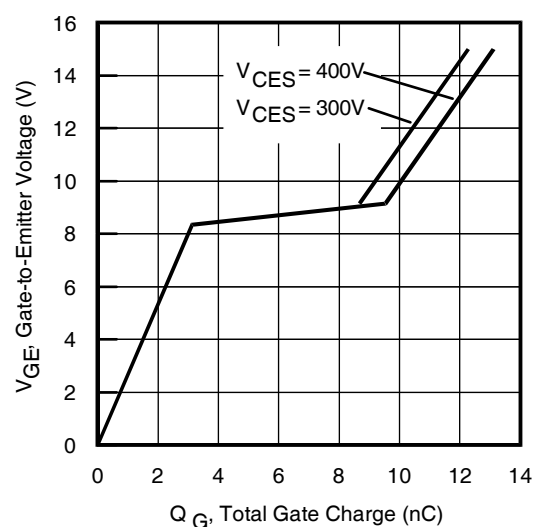
**Fig. 21** - Typical Diode  $E_{RR}$  vs.  $I_F$   
 $T_J = 175^\circ C$



**Fig. 22** - Typ.  $V_{GE}$  vs. Short Circuit Time  
 $V_{CC} = 400V$ ,  $T_C = 25^\circ C$



**Fig. 23** - Typ. Capacitance vs.  $V_{CE}$   
 $V_{GE} = 0V$ ;  $f = 1MHz$



**Fig. 24** - Typical Gate Charge vs.  $V_{GE}$   
 $I_{CE} = 6.0A$ ,  $L = 600\mu H$

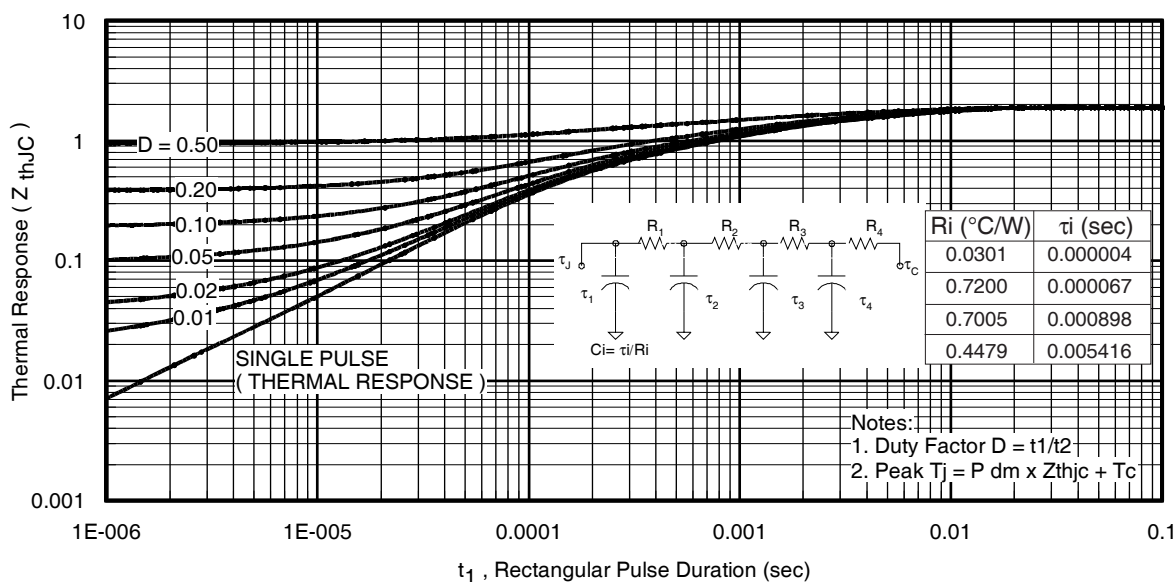


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

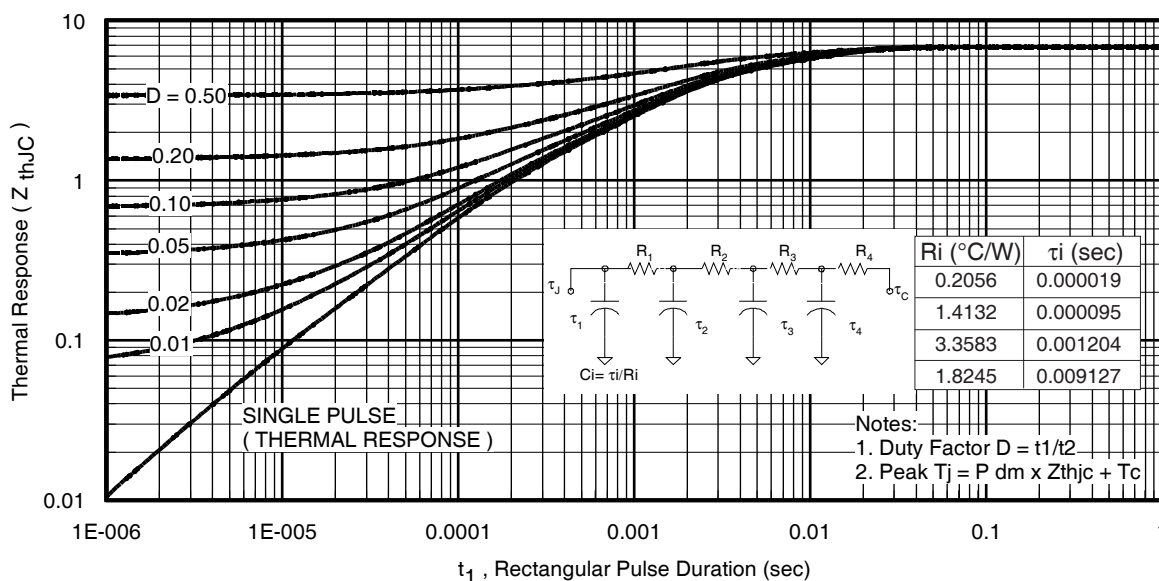
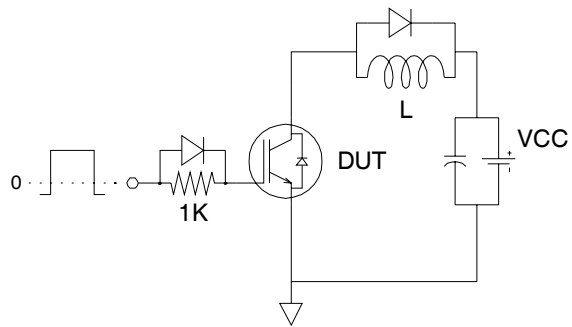
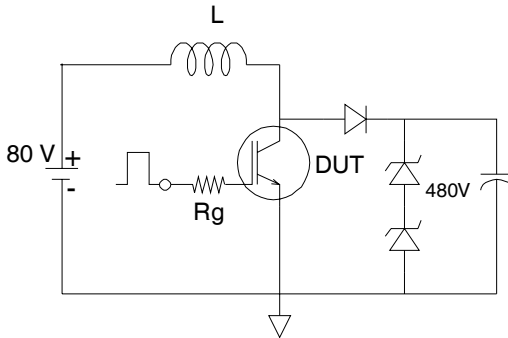


Fig 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

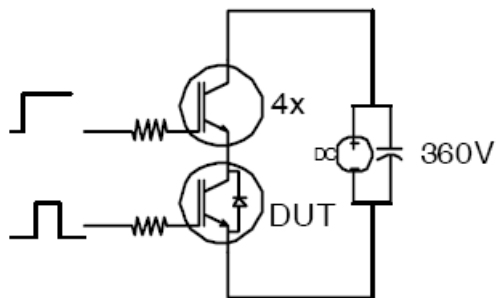




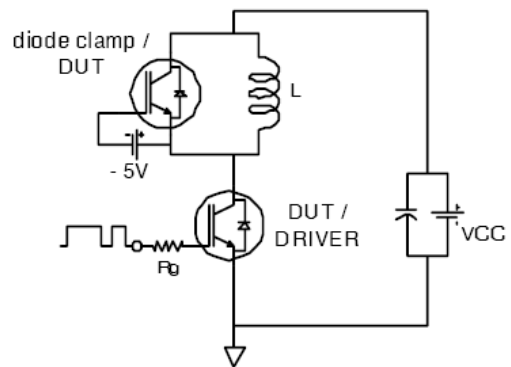
**Fig.C.T.1** - Gate Charge Circuit (turn-off)



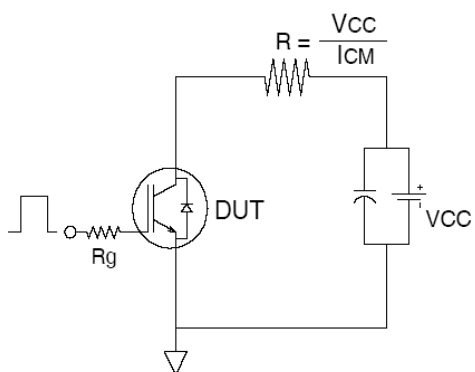
**Fig.C.T.2** - RBSOA Circuit



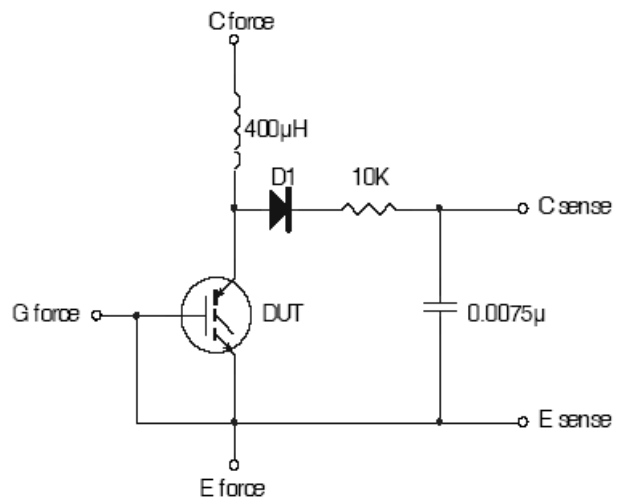
**Fig.C.T.3** - S.C.SOA Circuit



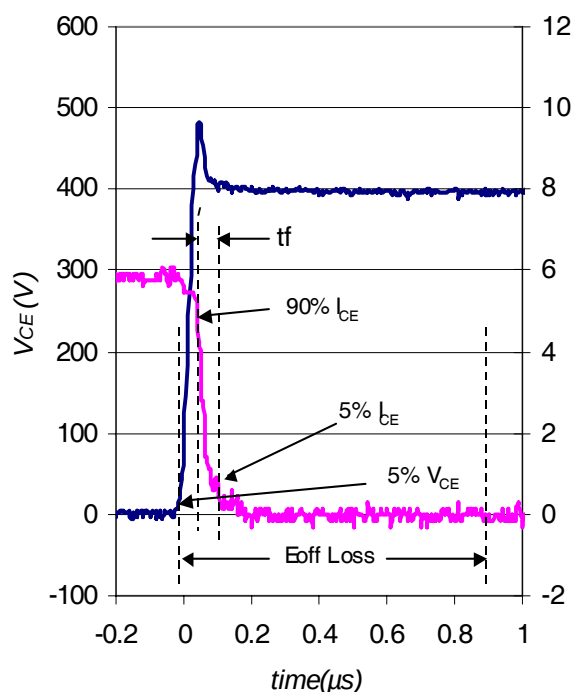
**Fig.C.T.4** - Switching Loss Circuit



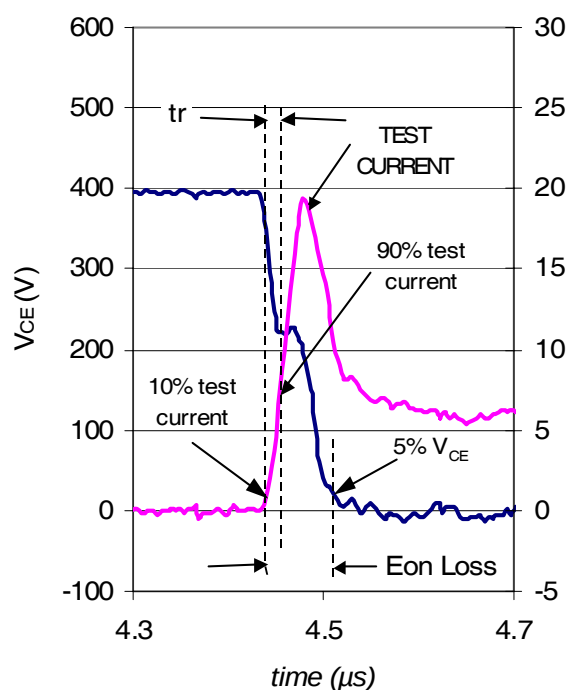
**Fig.C.T.5** - Resistive Load Circuit



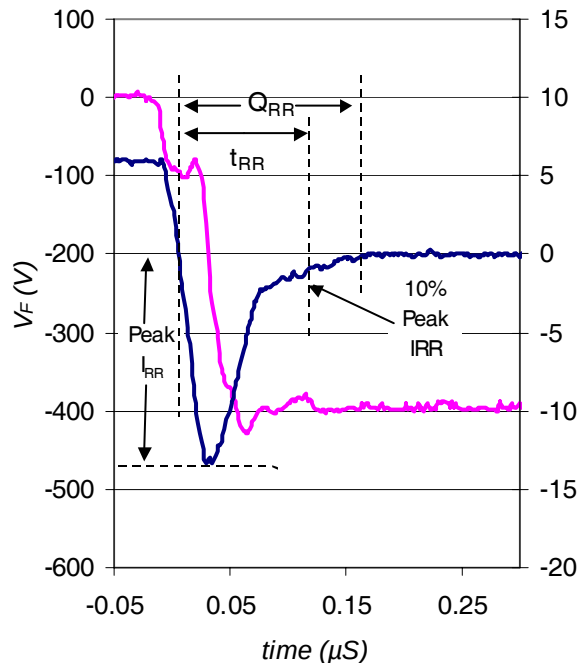
**Fig.C.T.6** - Typical Filter Circuit for  $V_{(BR)CES}$  Measurement



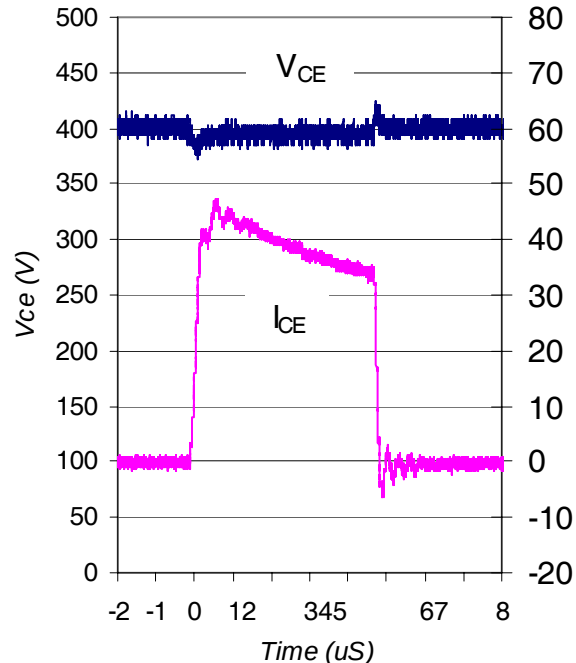
**Fig. WF1** - Typ. Turn-off Loss Waveform  
@  $T_J = 175^\circ\text{C}$  using Fig. CT.4



**Fig. WF2** - Typ. Turn-on Loss Waveform  
@  $T_J = 175^\circ\text{C}$  using Fig. CT.4



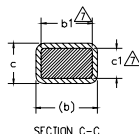
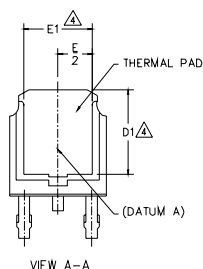
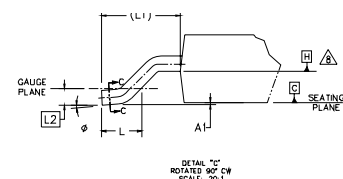
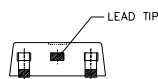
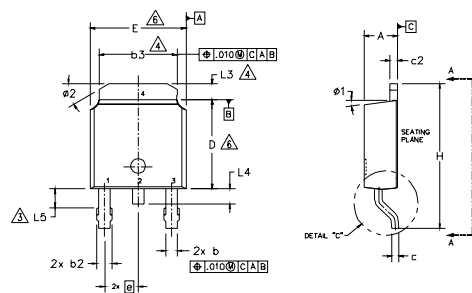
**WF.3-** Typ. Diode Recovery Waveform  
@  $T_J = 175^\circ\text{C}$  using CT.4



**WF.4-** Typ. Short Circuit Waveform  
@  $T_J = 25^\circ\text{C}$  using CT.3

## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



### NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
- 3.- LEAD DIMENSION UNCONTROLLED IN L5.
- 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

| SYMBOL | DIMENSIONS  |       |           |      | NOTES |
|--------|-------------|-------|-----------|------|-------|
|        | MILLIMETERS |       | INCHES    |      |       |
|        | MIN.        | MAX.  | MIN.      | MAX. |       |
| A      | 2.18        | 2.39  | .086      | .094 |       |
| A1     | —           | 0.13  | —         | .005 |       |
| b      | 0.64        | 0.89  | .025      | .035 |       |
| b1     | 0.65        | 0.79  | .025      | .031 | 7     |
| b2     | 0.76        | 1.14  | .030      | .045 |       |
| b3     | 4.95        | 5.46  | .195      | .215 | 4     |
| c      | 0.46        | 0.61  | .018      | .024 |       |
| c1     | 0.41        | 0.56  | .016      | .022 | 7     |
| c2     | 0.46        | 0.89  | .018      | .035 |       |
| D      | 5.97        | 6.22  | .235      | .245 | 6     |
| D1     | 5.21        | —     | .205      | —    | 4     |
| E      | 6.35        | 6.73  | .250      | .265 | 6     |
| E1     | 4.32        | —     | .170      | —    | 4     |
| e      | 2.29 BSC    |       | .090 BSC  |      |       |
| H      | 9.40        | 10.41 | .370      | .410 |       |
| L      | 1.40        | 1.78  | .055      | .070 |       |
| L1     | 2.74 BSC    |       | .108 REF. |      |       |
| L2     | 0.51 BSC    |       | .020 BSC  |      |       |
| L3     | 0.89        | 1.27  | .035      | .050 | 4     |
| L4     | —           | 1.02  | —         | .040 |       |
| L5     | 1.14        | 1.52  | .045      | .060 | 3     |
| ø      | 0"          | 10"   | 0"        | 10"  |       |
| ø1     | 0"          | 15"   | 0"        | 15"  |       |
| ø2     | 25"         | 35"   | 25"       | 35"  |       |

### LEAD ASSIGNMENTS

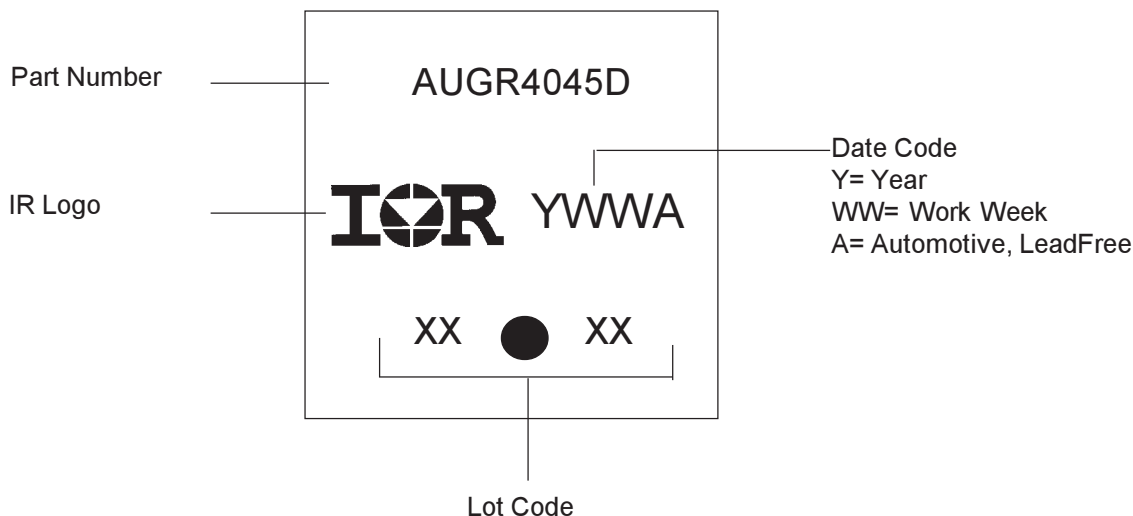
### HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

### IGBT & CoPAK

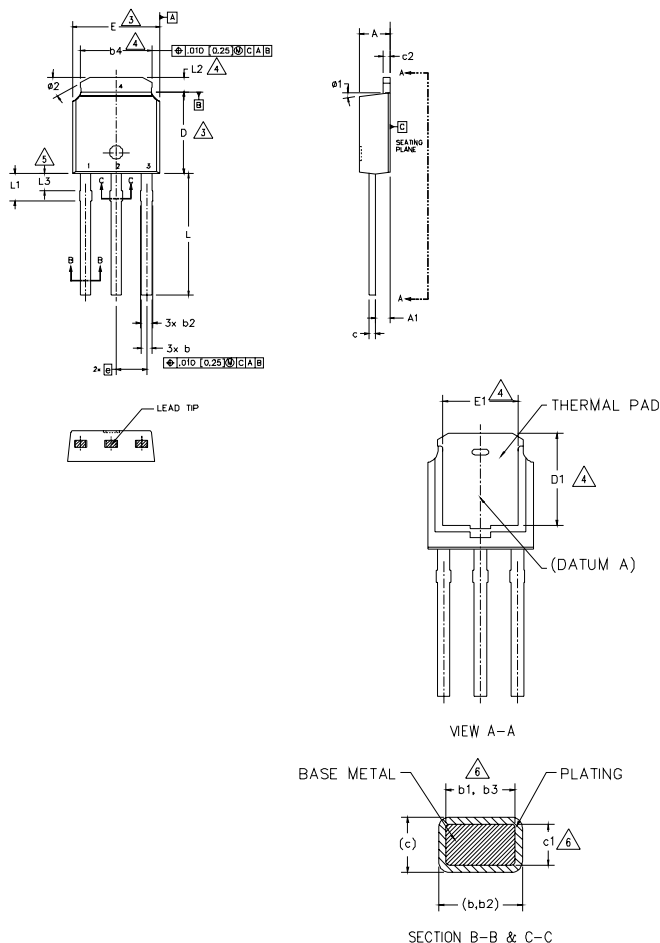
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

## D-Pak Part Marking Information



## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



### NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
- △ DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- △- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- △- LEAD DIMENSION UNCONTROLLED IN L3.
- △- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
- 8.- CONTROLLING DIMENSION : INCHES.

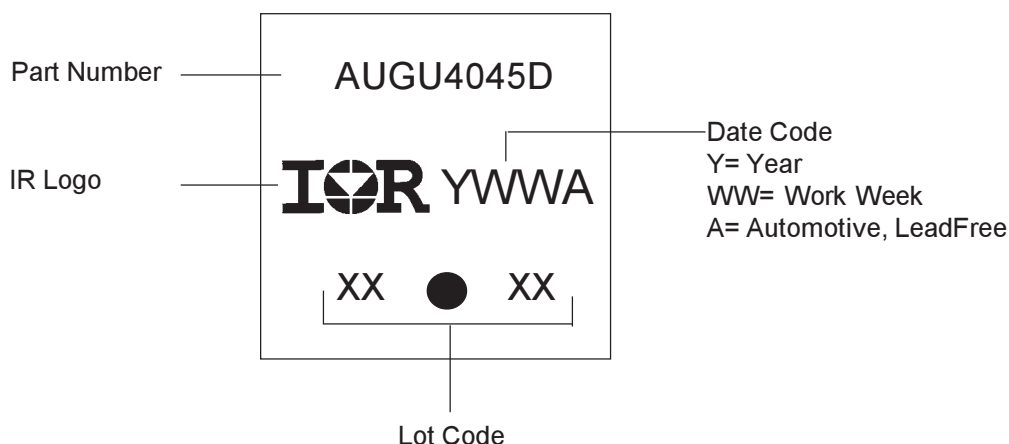
| S<br>Y<br>M<br>B<br>O<br>L | DIMENSIONS  |      |          |      | N<br>O<br>T<br>E<br>S |
|----------------------------|-------------|------|----------|------|-----------------------|
|                            | MILLIMETERS |      | INCHES   |      |                       |
|                            |             |      | MIN.     | MAX. |                       |
| A                          | 2.18        | 2.39 | .086     | .094 | 6                     |
| A1                         | 0.89        | 1.14 | .035     | .045 |                       |
| b                          | 0.64        | 0.89 | .025     | .035 |                       |
| b1                         | 0.65        | 0.79 | .025     | .031 | 6                     |
| b2                         | 0.76        | 1.14 | .030     | .045 |                       |
| b3                         | 0.76        | 1.04 | .030     | .041 |                       |
| b4                         | 4.95        | 5.46 | .195     | .215 | 4                     |
| c                          | 0.46        | 0.61 | .018     | .024 |                       |
| c1                         | 0.41        | 0.56 | .016     | .022 |                       |
| c2                         | 0.46        | 0.89 | .018     | .035 | 6                     |
| D                          | 5.97        | 6.22 | .235     | .245 |                       |
| D1                         | 5.21        | —    | .205     | —    |                       |
| E                          | 6.35        | 6.73 | .250     | .265 | 3                     |
| E1                         | 4.32        | —    | .170     | —    |                       |
| e                          | 2.29 BSC    |      | .090 BSC |      |                       |
| L                          | 8.89        | 9.65 | .350     | .380 | 4                     |
| L1                         | 1.91        | 2.29 | .045     | .090 |                       |
| L2                         | 0.89        | 1.27 | .035     | .050 |                       |
| L3                         | 1.14        | 1.52 | .045     | .060 | 5                     |
| ø1                         | 0"          | 15"  | 0"       | 15"  |                       |
| ø2                         | 25"         | 35"  | 25"      | 35"  |                       |

### LEAD ASSIGNMENTS

### HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

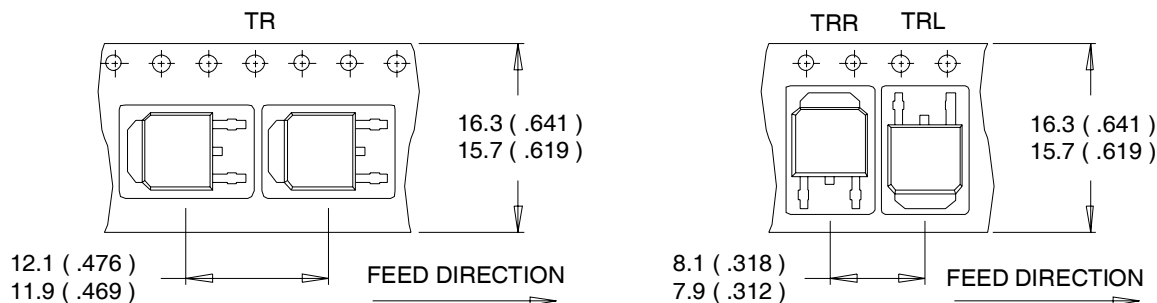
## I-Pak Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

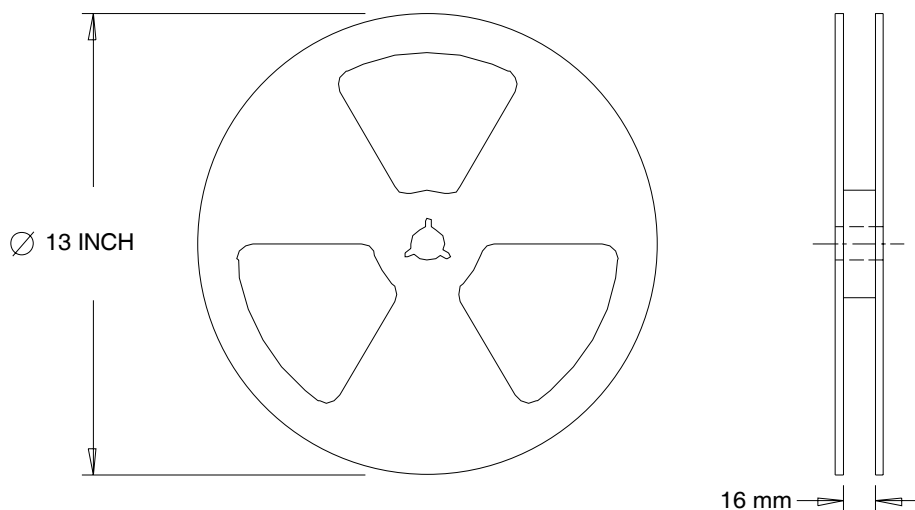
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



### NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



### NOTES :

1. OUTLINE CONFORMS TO EIA-481.

## Ordering Information

| Base part number | Package Type | Standard Pack       |          | Complete Part Number |
|------------------|--------------|---------------------|----------|----------------------|
|                  |              | Form                | Quantity |                      |
| AUIRGR4045D      | Dpak         | Tube                | 75       | AUIRGR4045D          |
|                  |              | Tape and Reel       | 2000     | AUIRGR4045DTR        |
|                  |              | Tape and Reel Left  | 3000     | AUIRGR4045DTRL       |
|                  |              | Tape and Reel Right | 3000     | AUIRGR4045DTRR       |
| AUIRGU4045D      | Ipak         | Tube                | 75       | AUIRGU4045D          |
|                  |              |                     |          |                      |
|                  |              |                     |          |                      |
|                  |              |                     |          |                      |

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